

# 1MBI1400VXB-120PL-54

IGBT Modules

## IGBT MODULE (V series) 1200V / 1400A / 1 in one package

### ■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

### ■ Applications

- NPC 3-level Inverter
- Active PFC
- Industrial machines



### ■ Maximum Ratings and Characteristics

#### ● Absolute Maximum Ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units	
Collector-Emitter voltage	$V_{CES}$		1200	V	
Gate-Emitter voltage	$V_{GES}$		$\pm 20$	V	
Collector current	$I_c$	Continuous	$T_c=25^\circ\text{C}$ 1800	A	
	$I_c$ pluse	1ms	$T_c=100^\circ\text{C}$ 1400		
	$-I_c$		2800		
	$-I_c$ pluse	1ms	1400		
Collector Power Dissipation	$P_c$	1 device	2800	W	
Reverse voltage for FWD	$V_R$		1200	V	
Forword current for FWD	$I_F$	Continuous	1400	A	
	$I_F$ pulse	1ms	2800		
Junction temperature	$T_j$		175	°C	
Operating junction temperature (under switching conditions)	$T_{jop}$		150		
Case temperature	$T_c$		150		
Storage temperature	$T_{stg}$		-40 ~ +150		
Isolation voltage	between terminal and copper base (*1)	$V_{iso}$	AC : 1min.	4000	VAC
	between thermistor and others (*2)				
Screw Torque (*3)	Mounting	-	M5	6.0	N m
	Main Terminals	-	M8	10.0	
	Sense Terminals	-	M4	2.1	

Note \*1: All terminals should be connected together during the test.

Note \*2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note \*3: Recommendable Value : Mounting 3.0 ~ 6.0 Nm (M5)  
 Recommendable Value : Main Terminals 8.0 ~ 10.0 Nm (M8)  
 Recommendable Value : Sense Terminals 1.8 ~ 2.1 Nm (M4)

● Electrical characteristics (at T<sub>j</sub>= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units		
			min.	typ.	max.			
IGBT / Inverse Diode	Zero gate voltage collector current	I <sub>CEs</sub>	V <sub>CE</sub> = 1200V V <sub>GE</sub> = 0V	-	-	12.0	mA	
	Gate-Emitter leakage current	I <sub>GES</sub>	V <sub>CE</sub> = 0V V <sub>GE</sub> = ±20V	-	-	2400	nA	
	Gate-Emitter threshold voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> = 20V I <sub>c</sub> = 1400mA	6.0	6.5	7.0	V	
	Collector-Emitter saturation voltage ( with V <sub>CE(sat)</sub> classification : *5 )	V <sub>CE(sat)</sub> (terminal) (*4)	I <sub>c</sub> = 1400A V <sub>GE</sub> = 15V	T <sub>j</sub> = 25°C	-	1.75	2.20	V
				T <sub>j</sub> = 125°C	-	2.10	-	
		T <sub>j</sub> = 150°C		-	2.15	-		
		T <sub>j</sub> = 25°C		-	1.65	2.10		
		T <sub>j</sub> = 125°C		-	2.00	-		
	V <sub>CE(sat)</sub> (chip)	T <sub>j</sub> = 150°C	-	2.05	-			
	Internal gate resistance	R <sub>G(int)</sub>	-	-	0.79	-	Ω	
Input capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz	-	128	-	nF		
Turn-on time	t <sub>on</sub>	V <sub>CC</sub> = 600V I <sub>c</sub> = 1400A	-	1000	-	nsec		
	t <sub>r</sub>	V <sub>GE</sub> = ±15V	-	400	-			
	t <sub>r(f)</sub>	R <sub>G</sub> = +1 Ω	-	150	-			
	t <sub>off</sub>	L <sub>S</sub> = 60nH	-	1200	-			
Turn-off time	t <sub>r</sub>	-	-	150	-	nsec		
	t <sub>r</sub>	-	-	150	-			
Forward on voltage ( with V <sub>F</sub> classification : *5 )	V <sub>F</sub> (terminal) (*4)	I <sub>F</sub> = 1400A V <sub>GE</sub> = 0V	T <sub>j</sub> = 25°C	-	1.90	2.35	V	
			T <sub>j</sub> = 125°C	-	2.05	-		
	T <sub>j</sub> = 150°C		-	2.00	-			
	T <sub>j</sub> = 25°C		-	1.80	2.25			
	T <sub>j</sub> = 125°C		-	1.95	-			
V <sub>F</sub> (chip)	T <sub>j</sub> = 150°C	-	1.90	-				
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 1400A	-	200	-	nsec		
Reverse Current	I <sub>R</sub>	V <sub>CE</sub> = 1200V	-	-	6.0	mA		
FWD	V <sub>F</sub> (terminal) (*4)	I <sub>F</sub> = 1400A V <sub>GE</sub> = 0V	T <sub>j</sub> = 25°C	-	1.90	2.35	V	
			T <sub>j</sub> = 125°C	-	2.05	-		
	T <sub>j</sub> = 150°C		-	2.00	-			
	T <sub>j</sub> = 25°C		-	1.80	2.25			
	T <sub>j</sub> = 125°C		-	1.95	-			
V <sub>F</sub> (chip)	T <sub>j</sub> = 150°C	-	1.90	-				
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 1400A	-	200	-	nsec		
Thermistor	Resistance	R	T = 25°C	-	5000	-	Ω	
		R	T = 100°C	465	495	520		
B value	B	T = 25/50°C	3305	3375	3450	K		

Note \*4: Please refer to page 8 , there is definition of on-state voltage at terminal .

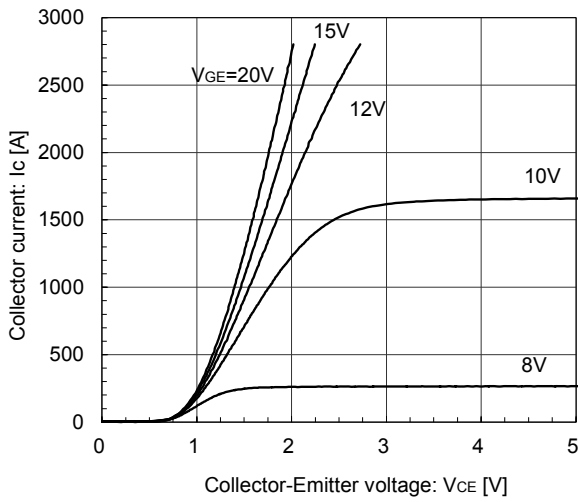
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance(1device)	R <sub>th(j-c)</sub>	Inverter IGBT	-	-	0.0195	°C/W
		Inverse Diode	-	-	0.0360	
		FWD	-	-	0.0360	
Contact thermal resistance (1device) (*5)	R <sub>th(c-f)</sub>	with Thermal Compound	-	0.00420	-	

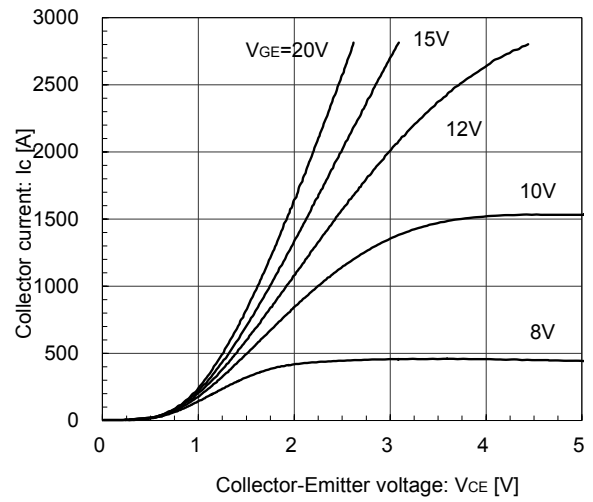
Note \*5: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

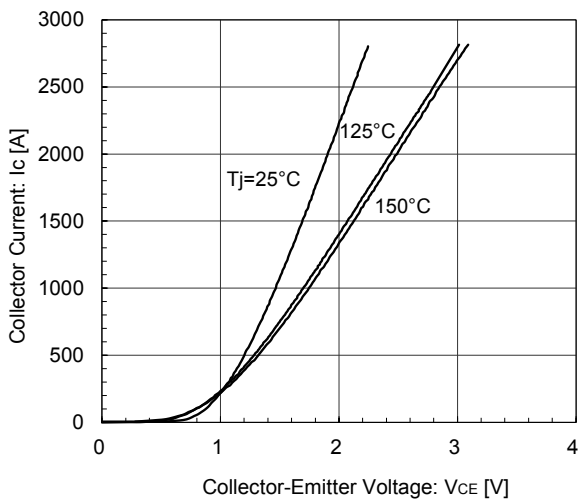
Collector current vs. Collector-Emmitter voltage (typ.)  
T<sub>j</sub> = 25°C / chip



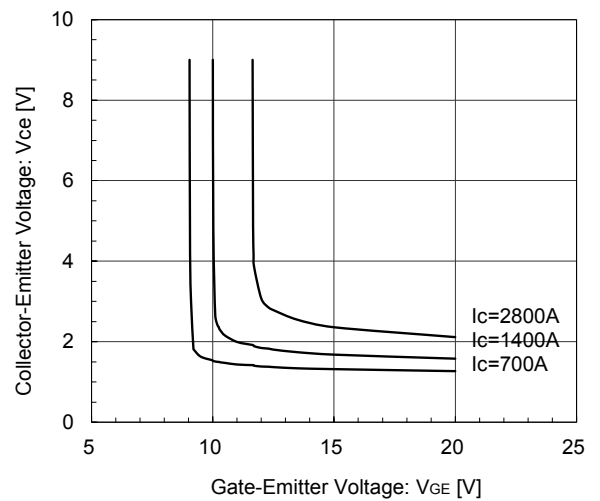
Collector current vs. Collector-Emmitter voltage (typ.)  
T<sub>j</sub> = 150°C / chip



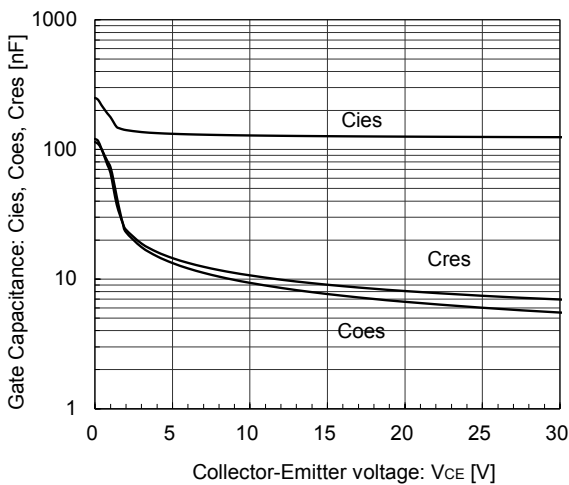
Collector current vs. Collector-Emmitter voltage (typ.)  
V<sub>GE</sub> = 15V / chip



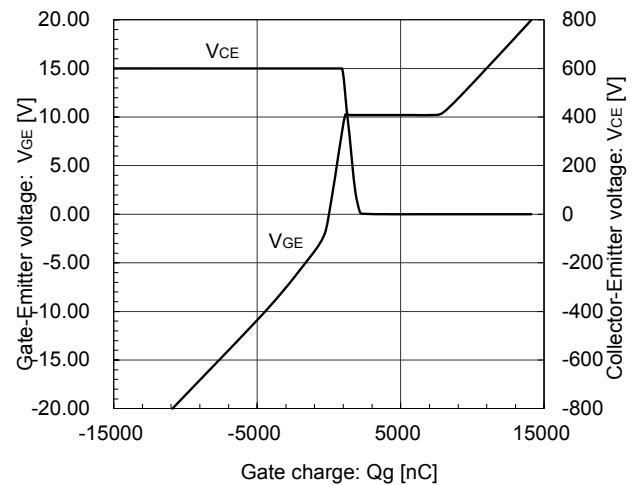
Collector-Emmitter voltage vs. Gate-Emmitter voltage (typ.)  
T<sub>j</sub> = 25°C / chip



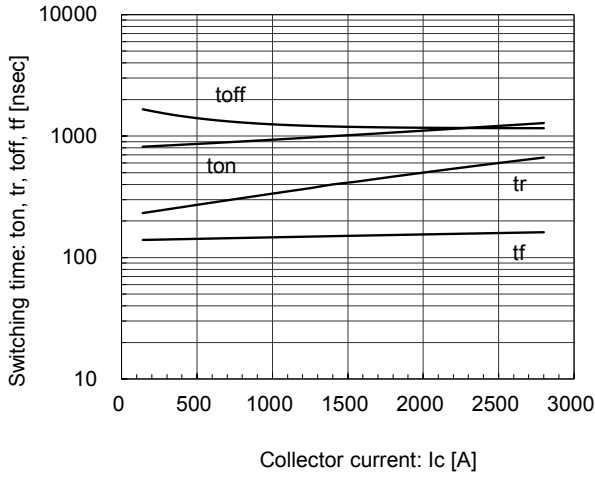
Gate Capacitance vs. Collector-Emmitter Voltage (typ.)  
V<sub>GE</sub> = 0V, f = 1MHz, T<sub>j</sub> = 25°C



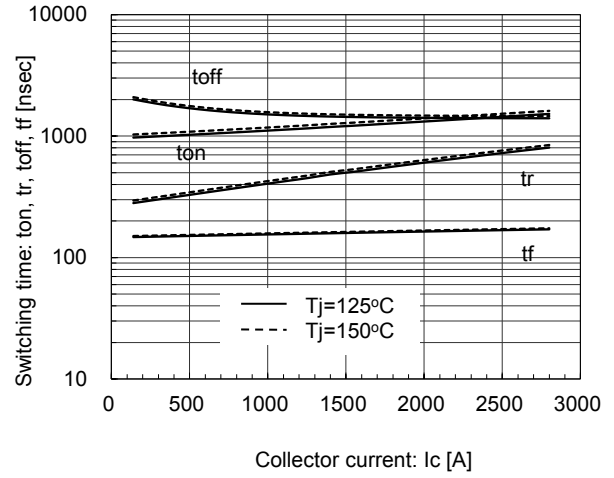
Dynamic Gate Charge (typ.)  
V<sub>CC</sub> = 600V, I<sub>c</sub> = 1400A, T<sub>j</sub> = 25°C



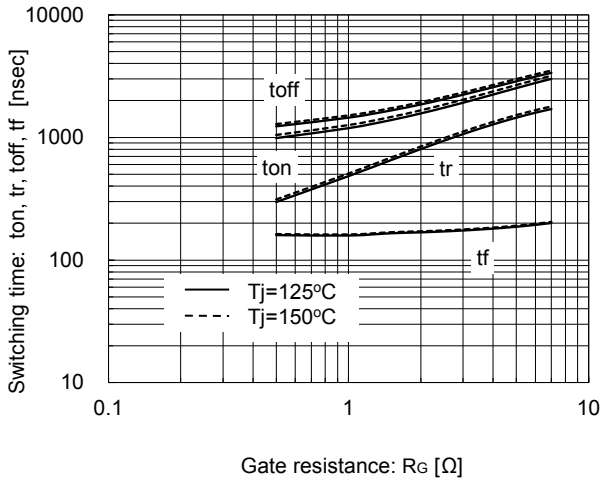
Switching time vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=15V, R_G=1\Omega, T_j=25^\circ C$



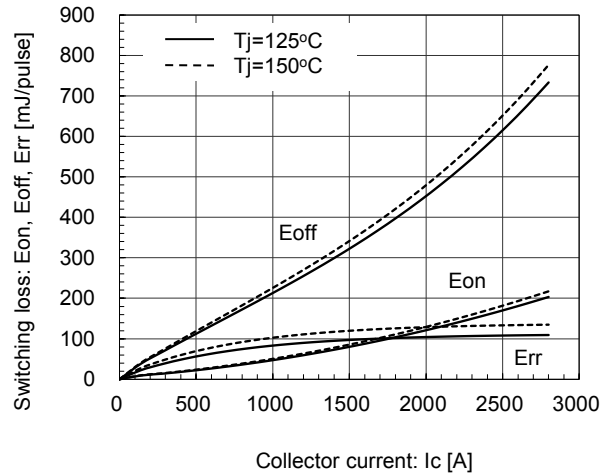
Switching time vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=15V, R_G=1\Omega, T_j=125^\circ C, 150^\circ C$



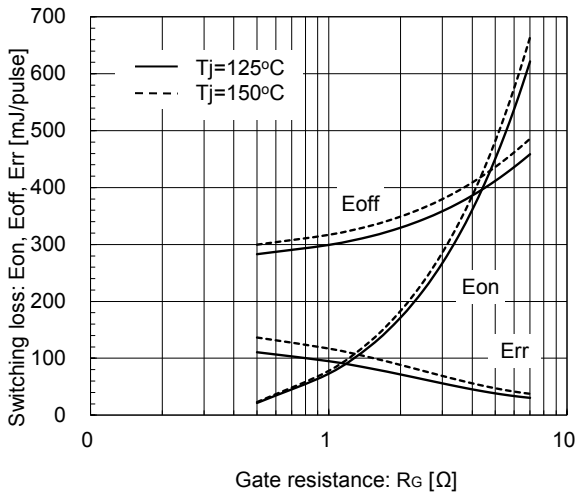
Switching time vs. Gate resistance (typ.)  
 $V_{CC}=600V, I_c=1400A, V_{GE}=\pm 15V, T_j=125^\circ C, 150^\circ C$



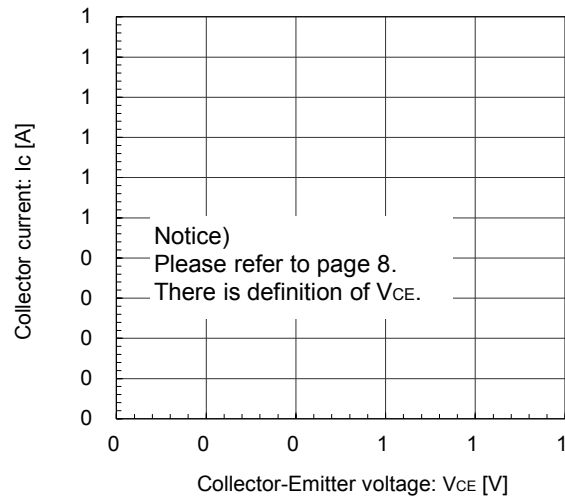
Switching loss vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=15V, R_G=1\Omega, T_j=125^\circ C, 150^\circ C$

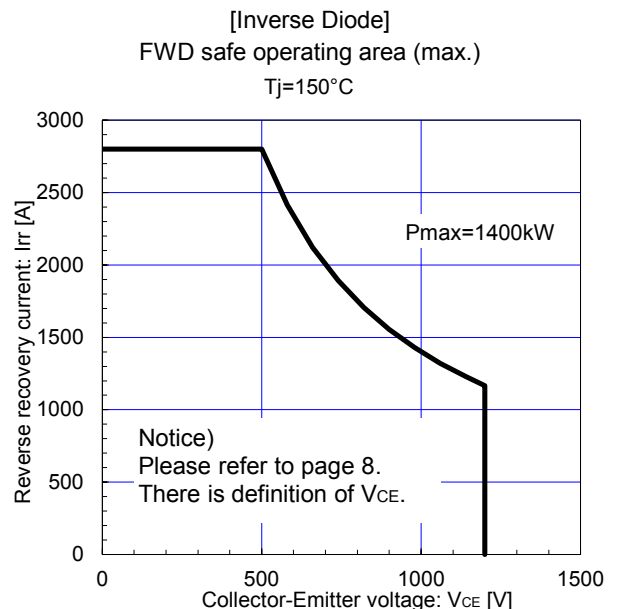
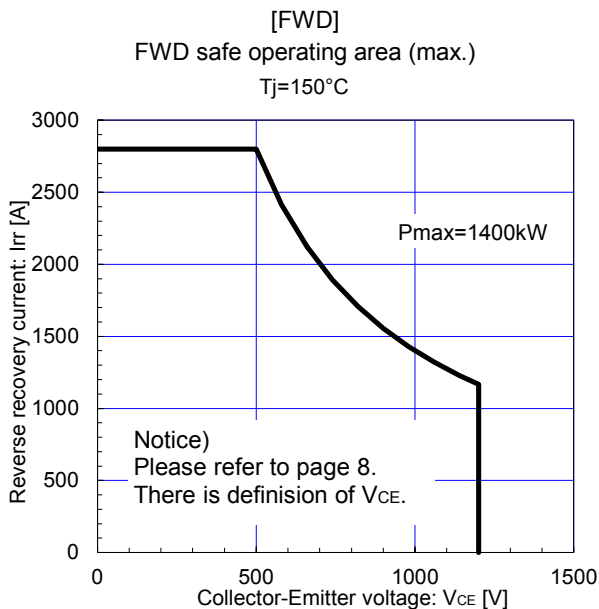
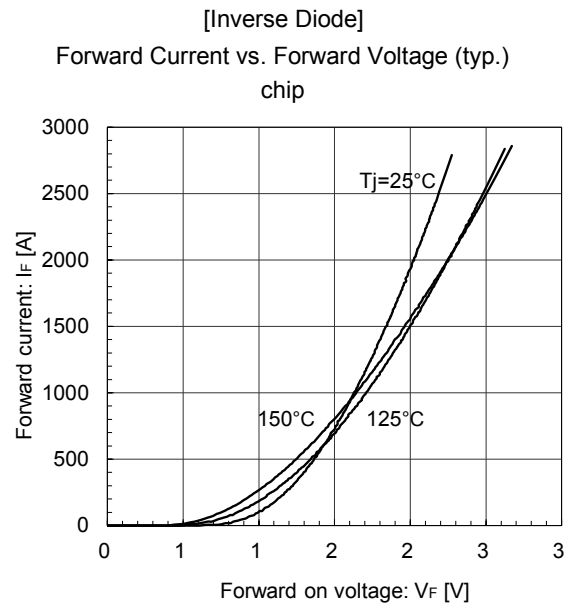
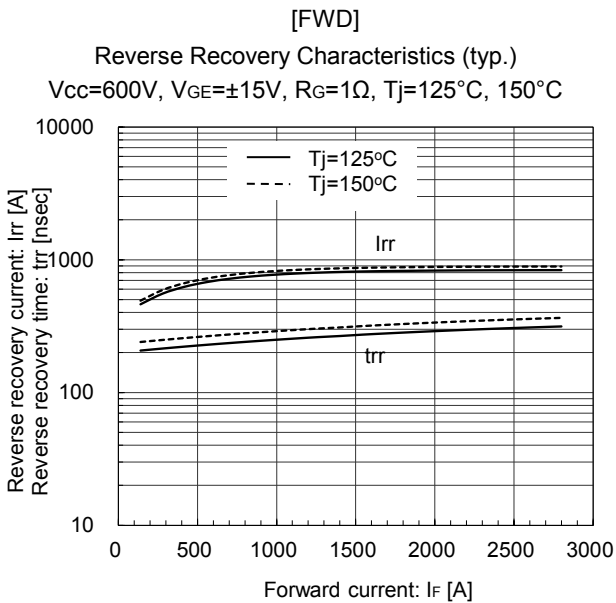
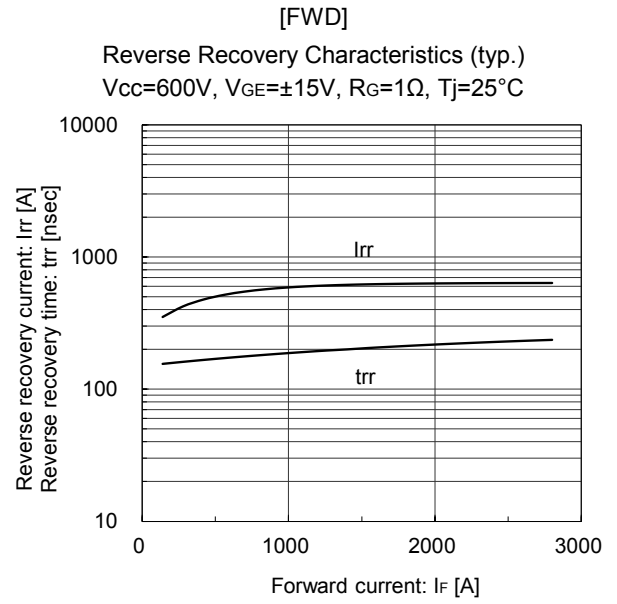
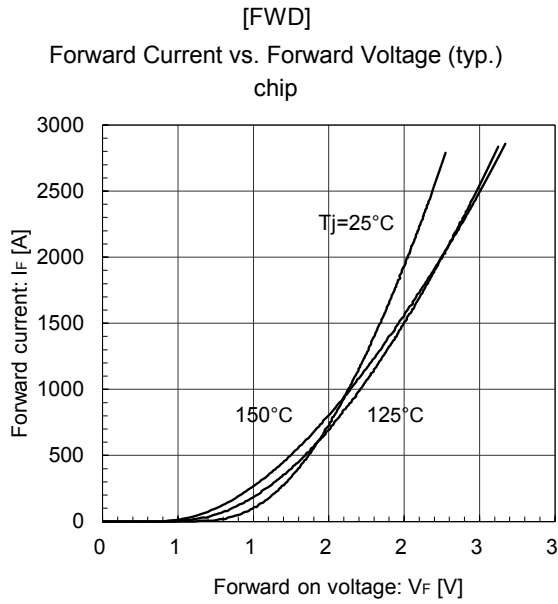


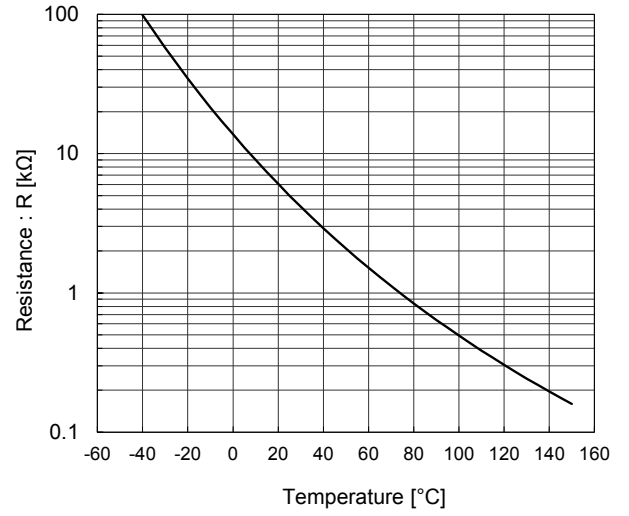
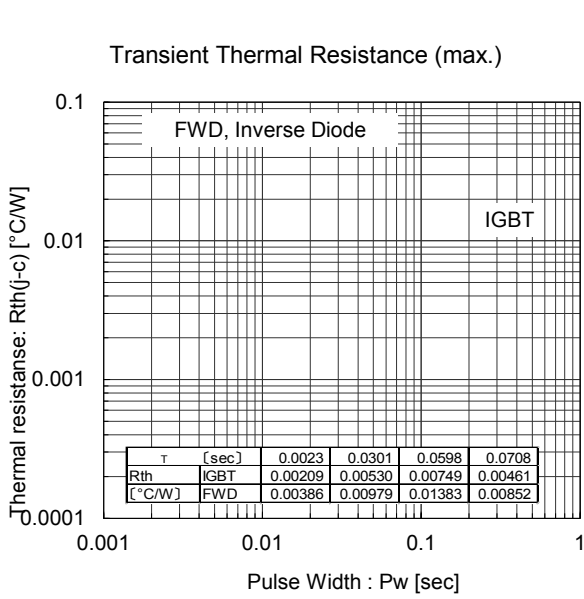
Switching loss vs. Gate resistance (typ.)  
 $V_{CC}=600V, I_c=1400A, V_{GE}=\pm 15V, T_j=125^\circ C, 150^\circ C$



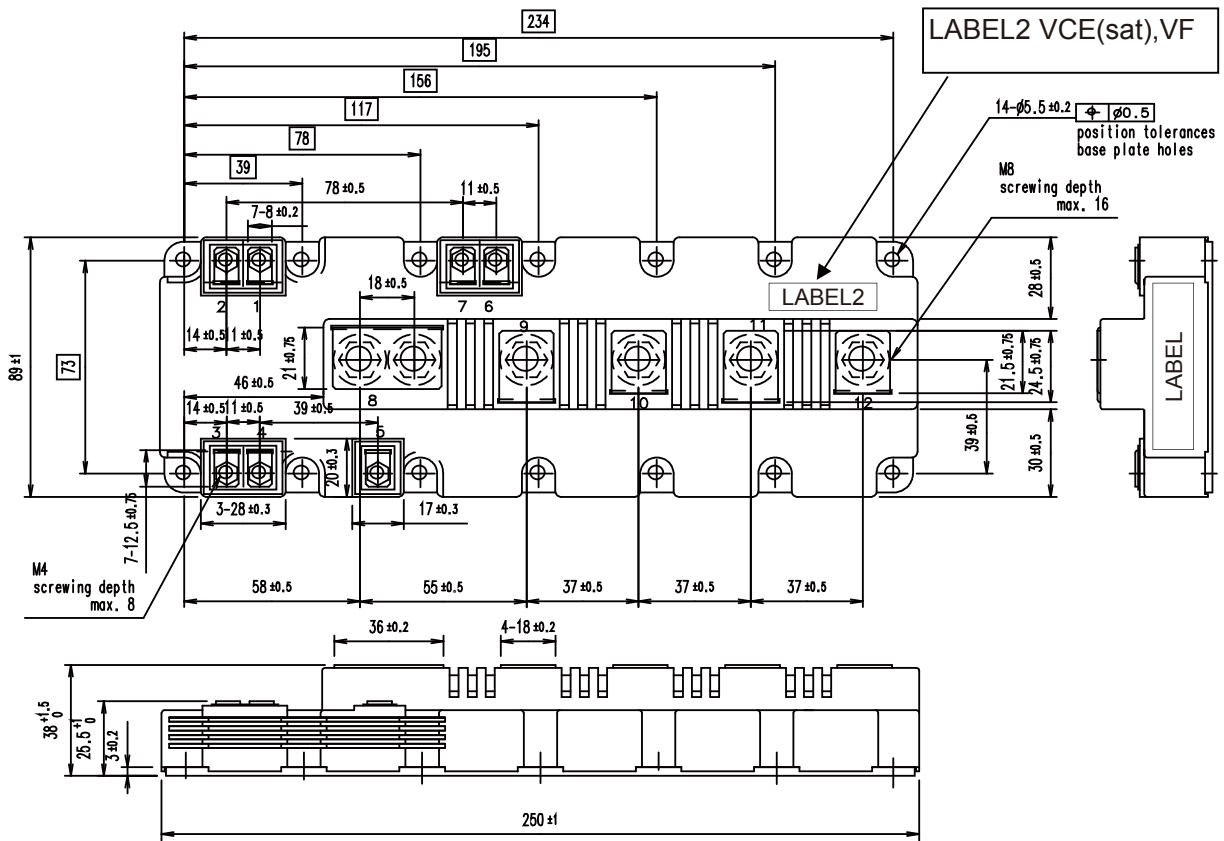
Reverse bias safe operating area (max.)  
 $+V_{GE}=15V, -V_{GE}=15V, R_G=1\Omega, T_j=150^\circ C$





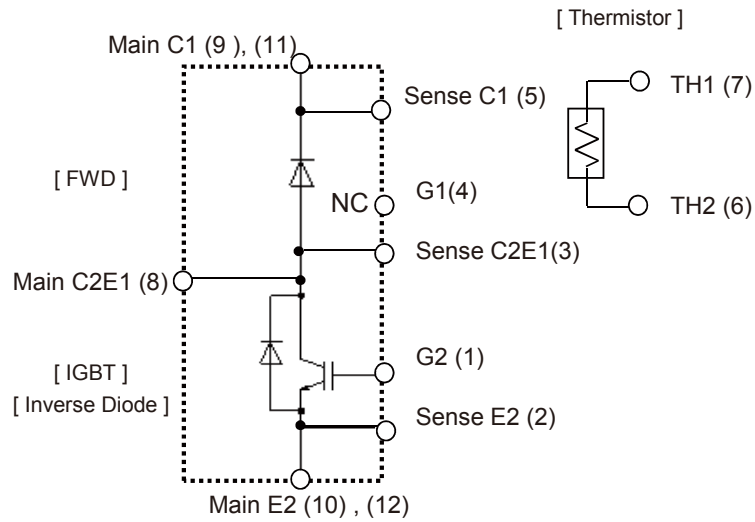


■ Outline Drawings, mm



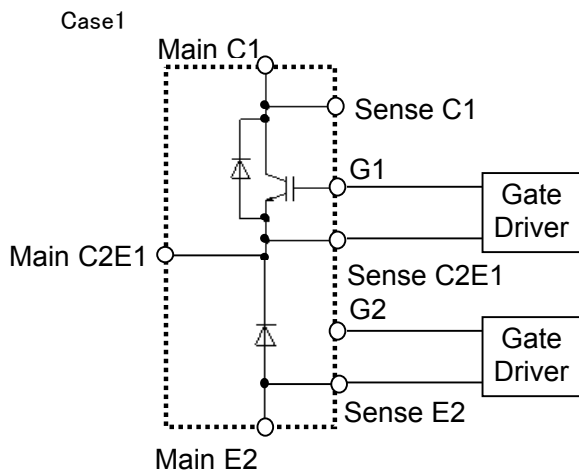
Weight: 1250g (typ.)

Equivalent Circuit Schematic

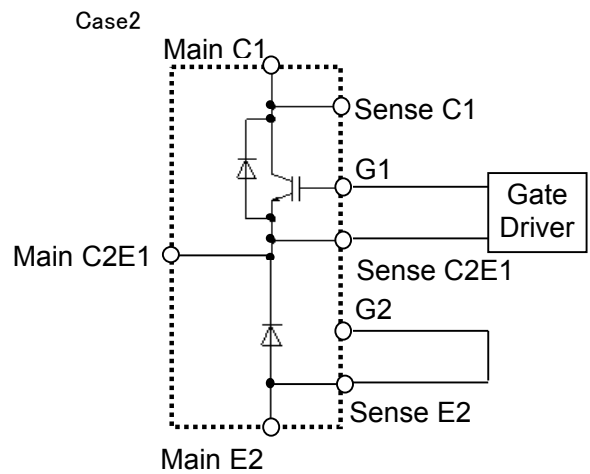


Notice) There is recommendation of wiring for NC terminal as follows

Fuji recommends wire connection of CASE1 or CASE2 to fix NC terminal voltage.

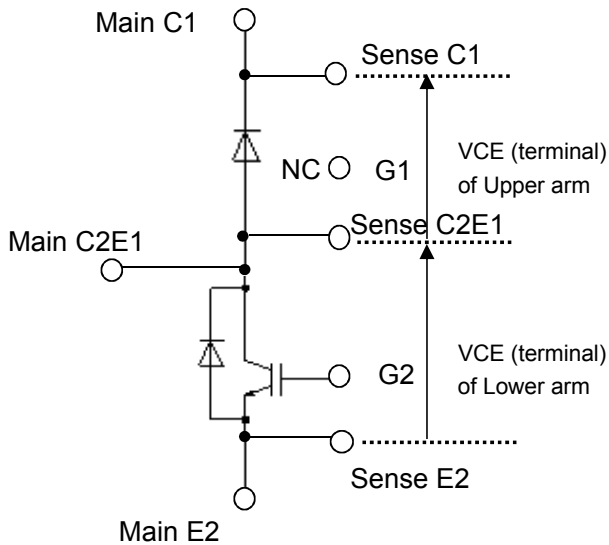


NC terminal (G2) and sense E2 should be connected by Gate-Driver.



NC terminal (G2) and sense E2 should be connected by wire.

## ■ Definition of on-state voltage at terminal and switching characteristics



Fuji defined VCE value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Switching characteristics of VCE also is defined between Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Please use these terminals whenever measure spike voltage and on-state voltage .

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